



### N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	Package	I <sub>D max</sub> T <sub>A</sub> = +25°C
	$52m\Omega$ @ $V_{GS}$ = $10V$		
30V	$65mΩ @ V_{GS} = 4.5V$	SOT323	4A
	85mΩ @ V <sub>GS</sub> = 2.5V		

### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Applications**

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays

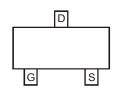
### **Mechanical Data**

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe.
  Solderable per MIL-STD-202, Method 208 3
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)

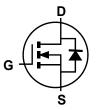
SOT323



Top View



Pin Configuration Top View



**Equivalent CircuitI** 

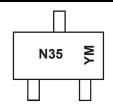
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3065LW-7	SOT323	3000/Tape & Reel
DMN3065LW-13	SOT323	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



N35 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	201	2	2013		2014	20	15	2016		2017		2018
Code	Z		Α		В	(	$\circ$	D		E		F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V <sub>DSS</sub>	30	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current (Note 5)	I <sub>D</sub>	4	Α
Body-Diode Continuous Current (Note 5)	Is	1	Α

# **Thermal Characteristics**

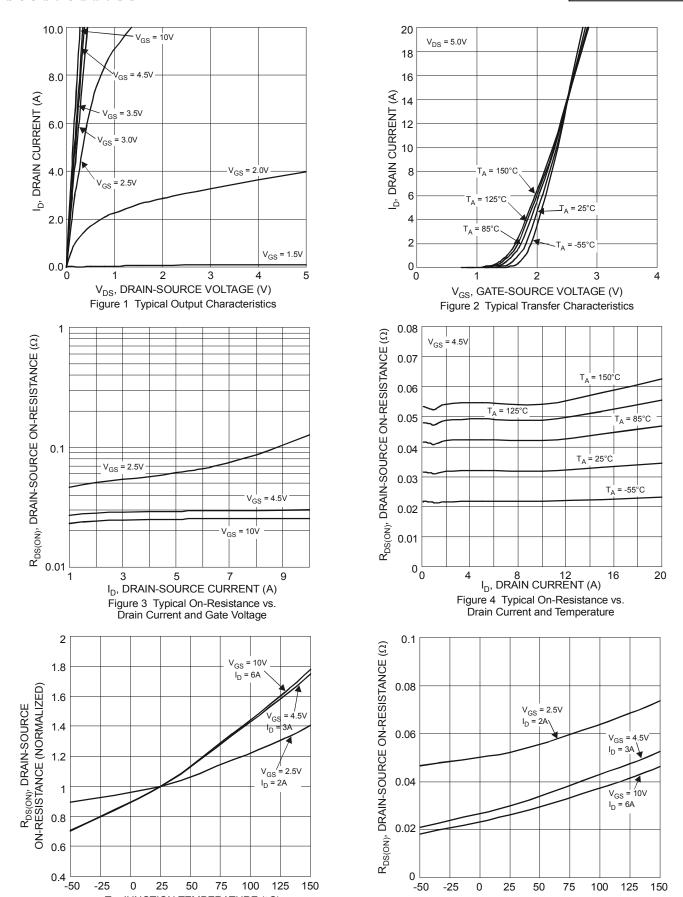
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$P_{D}$	770	mW	
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	$R_{\theta JA}$	162	°C/W	
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)	<u> </u>				ı		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μA	$V_{DS}$ = 30V, $V_{GS}$ = 0V	
Gate-Body Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	_	1.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			_	52		$V_{GS} = 10V, I_D = 4A$	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	_	_	65	mΩ	$V_{GS} = 4.5V, I_D = 3A$	
			_	85		$V_{GS} = 2.5V, I_D = 2A$	
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 2.0A$	
DYNAMIC CHARACTERISTICS(7)							
Input Capacitance	Ciss	_	465	_	pF	VDS = 15V, VGS = 0V, f = -1.0MHz	
Output Capacitance	Coss	_	49.5	_	pF		
Reverse Transfer Capacitance	Crss	_	43.8	_	pF	71.010112	
Gate Resistance	R <sub>g</sub>	_	2.3	_	Ω	$V_{DS}$ =0V, $V_{GS}$ = 0V, f = 1MHz	
Total Gate Charge (V <sub>GS</sub> =10V)	Qg	_	11.7	_	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 4 A	
Total Gate Charge (V <sub>GS</sub> =4.5V)	Qg	_	5.5	_	nC		
Gate-Source Charge	Q <sub>gs</sub>	_	1.1	_	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 4 A	
Gate-Drain Charge	$Q_{gd}$	_	1.8	_	nC	1	
Turn-On Delay Time	t <sub>D(on)</sub>	_	1.9	_	ns		
Turn-On Rise Time	tr	_	1.6	_	ns	V <sub>DD</sub> = 15V, V <sub>GEN</sub> = 10V,	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	10.3		ns	$R_{GEN} = 3\Omega$ , $R_L = 3.75\Omega$	
Turn-Off Fall Time	t <sub>f</sub>	_	2.0	_	ns		

 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing. Notes:





T<sub>.I</sub>, JUNCTION TEMPERATURE (°C)

Figure 5 On-Resistance Variation with Temperature

 $T_J$ , JUNCTION TEMPERATURE (°C)

Figure 6 On-Resistance Variation with Temperature



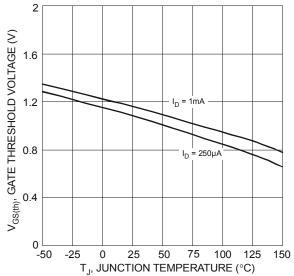
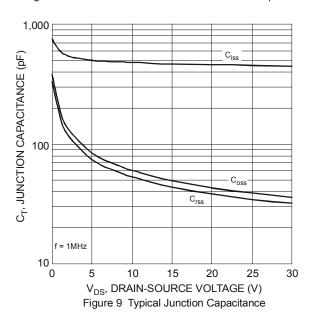
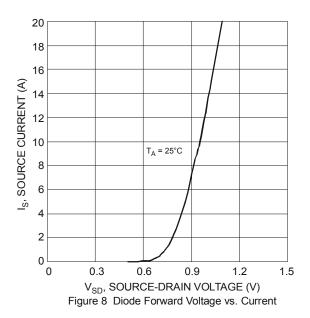
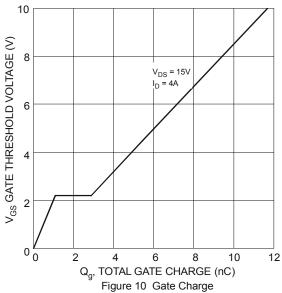


Figure 7 Gate Threshold Variation vs. Ambient Temperature

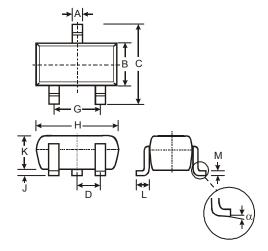






# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

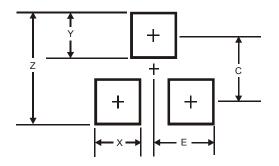


SOT323							
Dim	Min	Max	Тур				
Α	0.25	0.40	0.30				
В	1.15	1.35	1.30				
С	2.00	2.20	2.10				
D	-	-	0.65				
G	1.20	1.40	1.30				
Н	1.80	2.20	2.15				
J	0.0	0.10	0.05				
K	0.90	1.00	1.00				
L	0.25	0.40	0.30				
M	0.10	0.18	0.11				
α	0°	8°	-				
All	All Dimensions in mm						



## Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
Z	2.8			
Х	0.7			
Υ	0.9			
С	1.9			
E	1.0			

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